



### Description

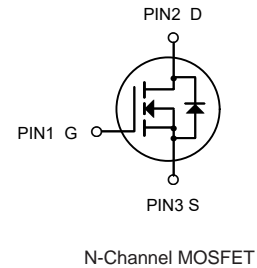
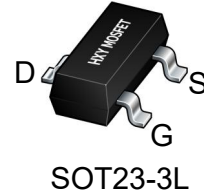
The AO3422-HXY uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

- $V_{DS} = 60V, I_D = 4.5A$
- $R_{DS(ON)} < 75m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 90m\Omega @ V_{GS}=4.5V$

### Application

- High power and current handing capability
- Lead free product is acquired
- Surface mount package
- PWM applications
- Load switch
- Power management



### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AO3422-HXY	SOT23-3L	ARDP 7B	3000PCS

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current-Continuous	4.5	A
$I_{DM}$	Drain Current-Pulsed (Note 1)	15	A
$P_D$	Maximum Power Dissipation	8	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	89	$^\circ C/W$



**Electrical Characteristics ( $T_J=25\text{ }^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=5A$	---	70	75	m $\Omega$
		$V_{GS}=4.5V, I_D=5A$	---	80	90	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^\circ C$	---	---	1	$\mu A$
		$V_{DS}=48V, V_{GS}=0V, T_J=55^\circ C$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$g_{fs}$	Forward Transconductance	$V_{DS}=5V, I_D=5A$	---	7	---	S
$Q_g$	Total Gate Charge (10V)	$V_{DS}=12V, V_{GS}=10V, I_D=5A$	---	5.5	---	nC
$Q_{gs}$	Gate-Source Charge		---	1.8	---	
$Q_{gd}$	Gate-Drain Charge		---	2.4	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=12V, V_{GS}=10V, R_G=3.3\Omega, I_D=5A$	---	6	---	ns
$T_r$	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
$T_f$	Fall Time		---	7	---	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	695	---	$\mu F$
$C_{oss}$	Output Capacitance		---	148	---	
$C_{rss}$	Reverse Transfer Capacitance		---	7	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V, \text{ Force Current}$	---	---	17	A
$I_{SM}$	Pulsed Source Current <sup>2,5</sup>		---	---	50	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=15A$
- 4.The power dissipation is limited by 150 $^\circ C$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



### Typical Characteristics

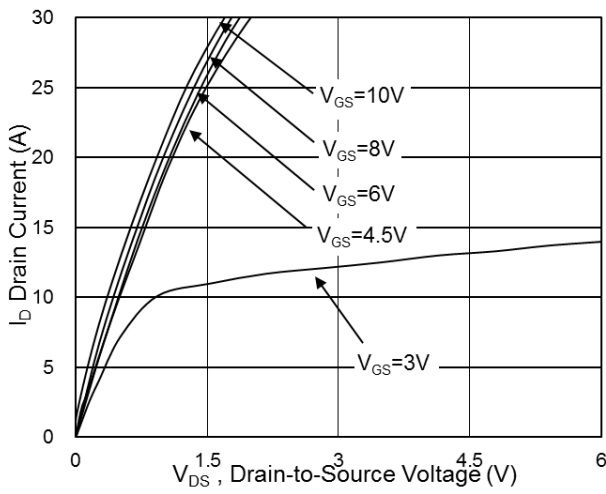


Fig.1 Typical Output Characteristics

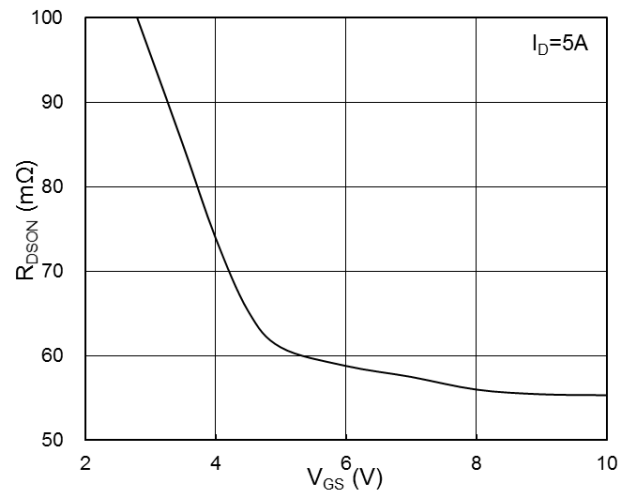


Fig.2 On-Resistance vs. Gate-Source Voltage

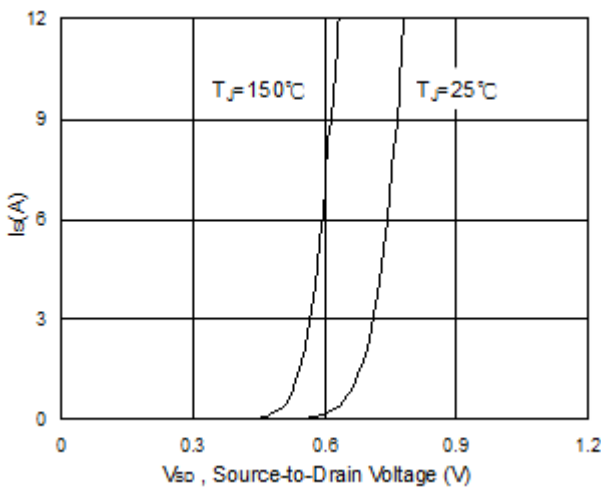


Fig.3 Forward Characteristics of Reverse

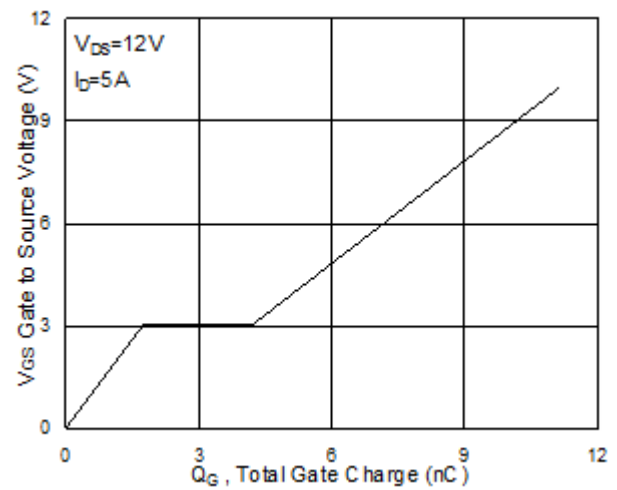


Fig.4 Gate-Charge Characteristics

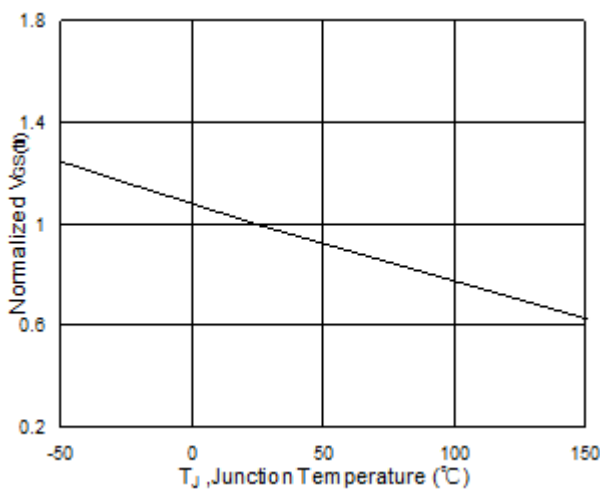


Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

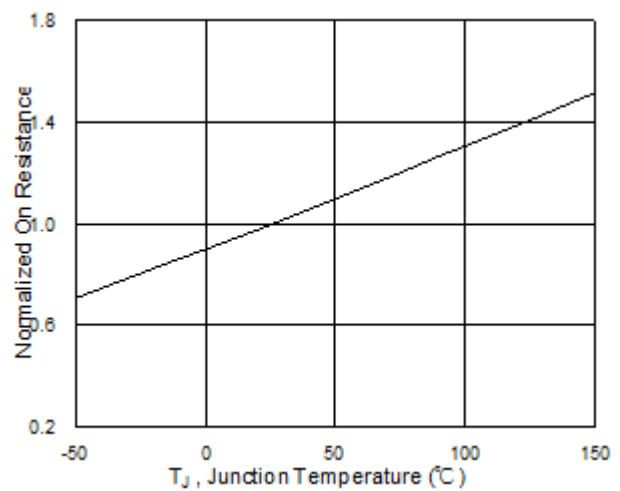


Fig.6 Normalized R<sub>DS(on)</sub> vs. T<sub>J</sub>

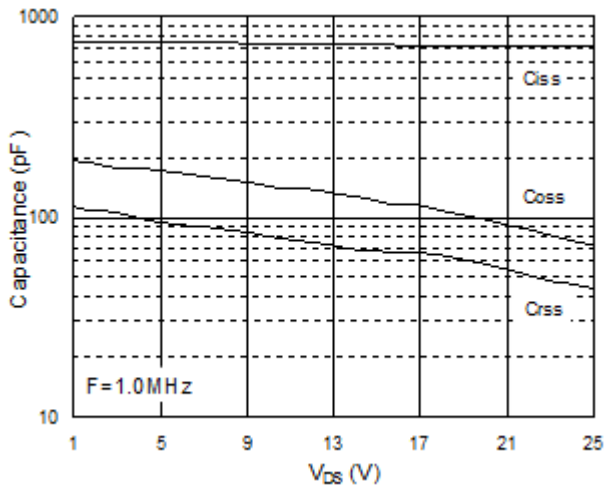


Fig.7 Capacitance

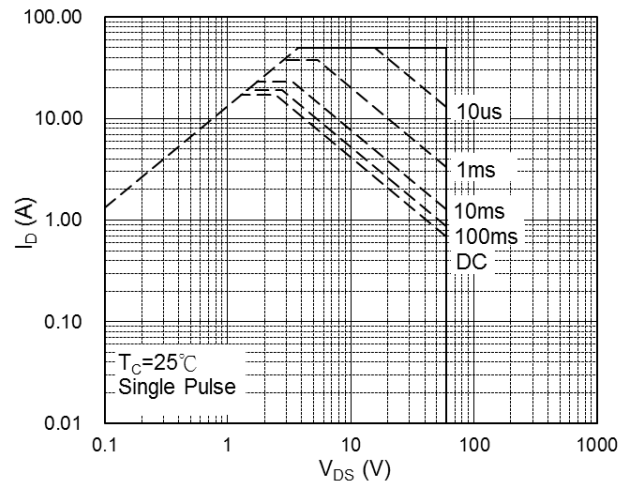


Fig.8 Safe Operating Area

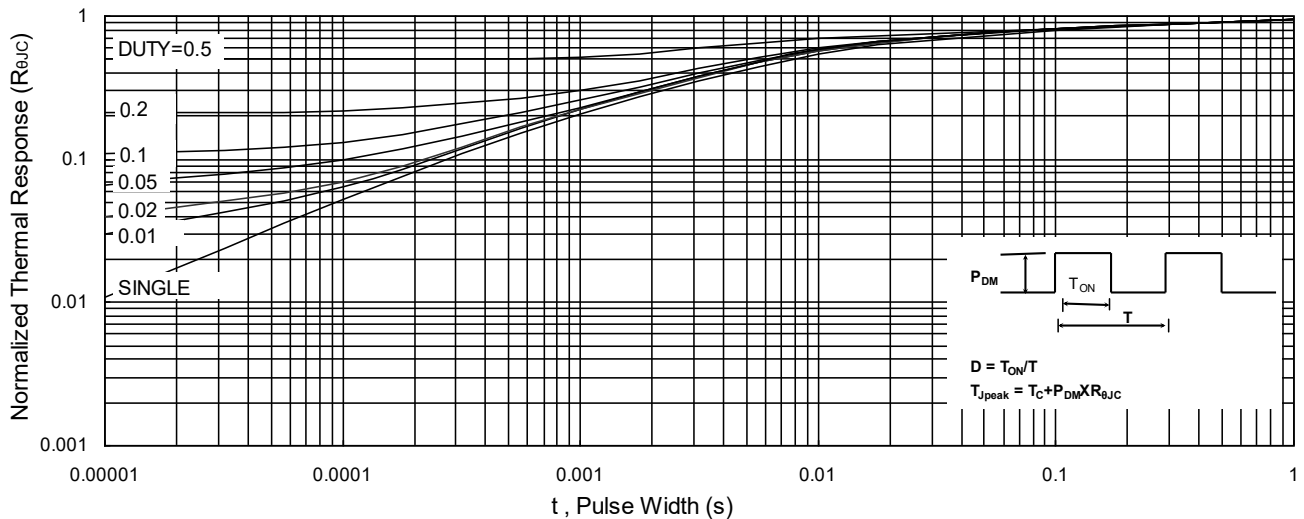


Fig.9 Normalized Maximum Transient Thermal Impedance

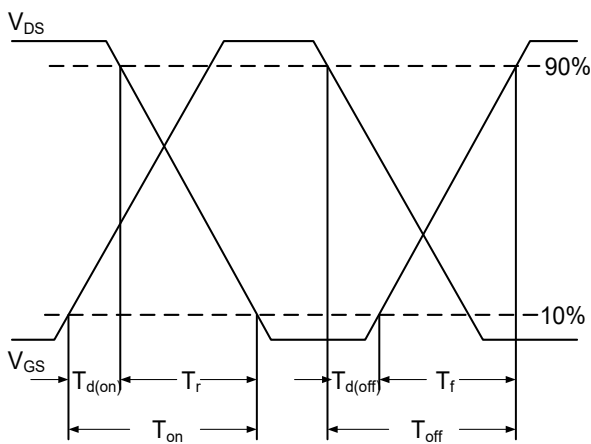


Fig.10 Switching Time Waveform

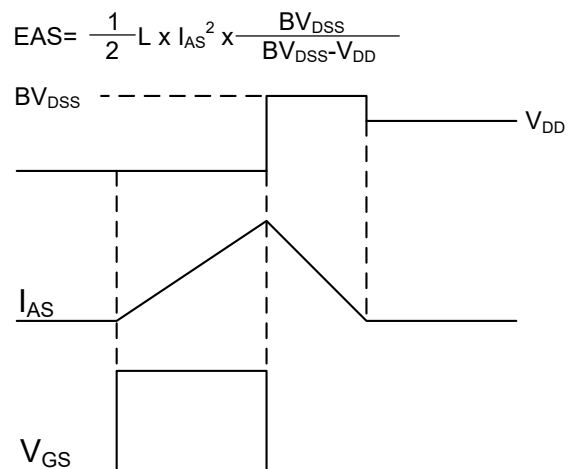
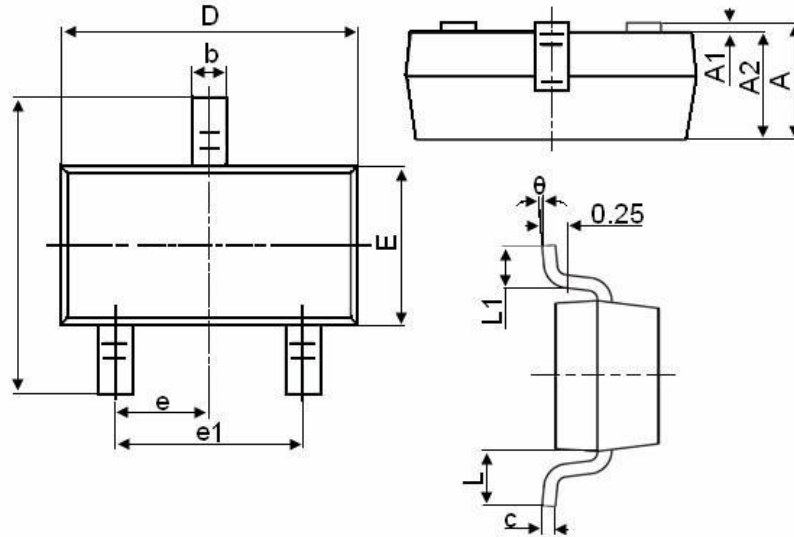


Fig.11 Unclamped Inductive Switching Waveform



### SOT23-3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°



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